



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

2SA673 TRANSISTOR (PNP)

FEATURE

Power dissipation

$$P_{CM} : 0.4 \text{ W (Tamb=25}^{\circ}\text{C)}$$

Collector current

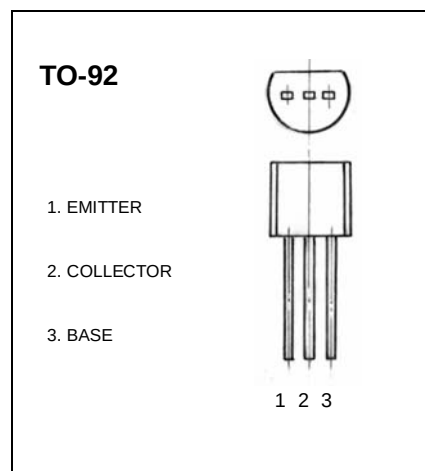
$$I_{CM} : -0.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -35 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55^{\circ}\text{C to } +150^{\circ}\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}$, $I_E = 0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 \text{ mA}$, $I_B = 0$	-35			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}$, $I_C = 0$	-4			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20 \text{ V}$, $I_E = 0$			-0.5	μA
DC current gain	$h_{FE(1)}^*$	$V_{CE} = -3 \text{ V}$, $I_C = -10 \text{ mA}$	60		320	
	$h_{FE(2)}$	$V_{CE} = -3 \text{ V}$, $I_C = -500 \text{ mA}$	10			
Collector-emitter saturation voltage	V_{CEsat}^*	$I_C = -150 \text{ mA}$, $I_B = -15 \text{ mA}$			-0.6	V
Base-emitter voltage	V_{BE}	$V_{CE} = -3 \text{ V}$, $I_C = -10 \text{ mA}$			-0.75	V

*Measured using pulse

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C	D
Range	60-120	100-200	160-320